3SK263

N-Channnel Dual Gate MOSFET 15V,30mA,PG=21dB,NF=1.1dB, CP4



Features

- · Enhancement type
- · Small noise figure
- · Small cross modulation

Specifications

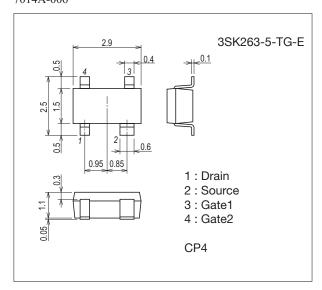
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDS		15	V
Gate1-to-Source Voltage	V _{G1S}		±8	V
Gate2-to-Source Voltage	V _{G2S}		±8	V
Drain Current	ID		30	mA
Allowable Power Dissipation	PD		200	mW
Channel Temperature	Tch		125	°C
Storage Temperature	Tstg		-55 to +125	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Package Dimensions

unit : mm (typ) 7014A-006



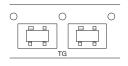
Product & Package Information

• Package : CP4

• JEITA, JEDEC : SC-61, SC-82AB, SOT-143, SOT-343

• Minimum Packing Quantity: 3,000 pcs./reel

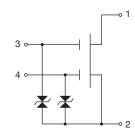
Packing Type: TG



Marking



Electrical Connection



Electrical Characteristics at Ta=25°C

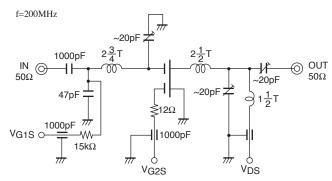
Parameter	Symbol	Conditions	Ratings			Unit
		Conditions	min	typ	max	Offic
Drain-to-Source Voltage	V _{DS}	V _{G1S} =0V, V _{G2S} =0V, I _D =100μA	15			V
Gate1-to-Source Cutoff Voltage	VG1S(off)	V _{DS} =6V, V _{G2S} =4V, I _D =100μA	0	0.7	1.3	V
Gate2-to-Source Cutoff Voltage	V _{G2S} (off)	V _{DS} =6V, V _{G1S} =3V, I _D =100μA	0.1	0.9	1.6	V
Gate1-to-Source Leakage Current	IG1SS	V _{G1S} =±6V, V _{G2S} =V _{DS} =0V			±50	nA
Gate2-to-Source Leakage Current	IG2SS	V _{G2S} =±6V, V _{G1S} =V _{DS} =0V			<u>±</u> 50	nA
Zero-Gate Voltage Drain Current	IDSX	V _{DS} =6V, V _{G1S} =1.5V, V _{G2S} =4V	*5		*12	mA
Forward Transfer Admittance	yfs	V _{DS} =6V, I _D =10mA, V _{G2S} =4V, f=1kHz		14		mS
Input Capacitance	Ciss	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		2.7		pF
Reverse Transfer Capacitance	Crss	V _{DS} =6V, f=1MHz, V _{G1S} =0V, V _{G2S} =4V		0.015	0.03	pF
Power Gain	PG	V _{DS} =6V, I _D =10mA, V _{G2S} =4V, f=200MHz	18	21		dB
Noise Figure	NF	V _{DS} =6V, I _D =10mA, V _{G2S} =4V, f=200MHz		1.1	2.2	dB

 $^{^{\}star}$: The 3SK263 is classified by IDSX as follows : (unit : mA)

Rank	5	
I _{DSX}	5.0 to 12.0	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

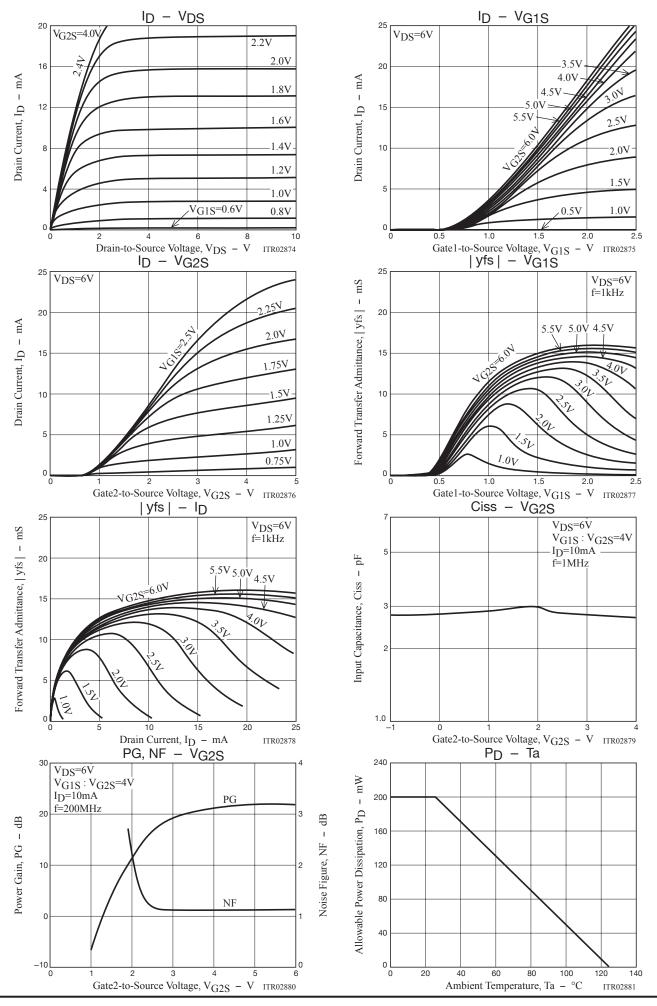
PG, NF Specified Test Circuit



L: 1mmØ enamel wire 10mmØ

Ordering Information

Device	Package	Shipping	memo	
3SK263-5-TG-E	CP4	3,000pcs./reel	Pb-Free	

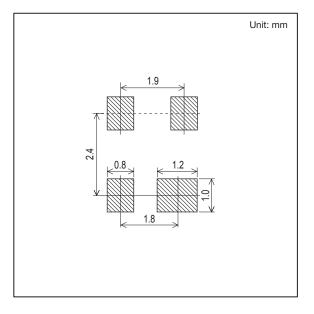


Outline Drawing

3SK263-5-TG-E

Mass (g) Unit 0.013 mm 2. 9±0. 15 0. 4+0.1 0. 5-0. 25 3 5±0.15 2, 5±0.2 0. 6^{+0. 1} 0. 5-0. 15 2 0.95 0.85 0.3±0.1 1. 1±0. 15 O. 1 S *1:Lot indication

Land Pattern Example



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